

**AMENDMENTS TO THE SPECIFICATION:**

Please amend the specification as follows:

Please insert the following after Paragraph [0024]:

Figure 7 is a cross sectional view of another device precursor according to the present invention.

Please inset the following after Paragraph [0058]:

Figure 7 illustrates a device precursor broadly designated at 30' including the silicon carbide substrate 15 and the n-type GaN layer 16. Figure 7 also illustrates a plurality of portions of p-type GaN (or depending upon the concentration n-type compensated GaN) designated at 31. Figure 7 also illustrates a plurality of portions of silicon dioxide layer 12 on the portions of the p-type Group III nitride layer 31. As also illustrated in Figure 7, device 30' further includes a respective portion of the source composition 13 on each of the silicon dioxide portions 12. Figure 7 further illustrates an embodiment of the invention in which second silicon dioxide layer 14 is limited to portions of source composition layer 13.